Product data sheet

1. Product profile

1.1 General description

High-voltage, high-speed planar-passivated NPN power switching transistor in a SOT186A (TO-220F) plastic package.

1.2 Features and benefits

- Fast switching
- High voltage capability

- Isolated package
- Low thermal resistance

1.3 Applications

- DC-to-DC converters
- High-frequency electronic lighting ballast applications
- Inverters
- Motor control systems

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _C	collector current	see Figure 1; see Figure 2; see Figure 4	-	-	4	Α
P _{tot}	total power dissipation	T _h ≤ 25 °C; see <u>Figure 3</u>	-	-	26	W
V _{CESM}	collector-emitter peak voltage	V _{BE} = 0 V	-	-	1050	V
Static chara	acteristics					
h _{FE}	DC current gain	$I_C = 0.1 \text{ A}; V_{CE} = 5 \text{ V}; T_h = 25 ^{\circ}C;$ see <u>Figure 11</u>	48	66	100	
		$I_C = 0.8 \text{ A}; V_{CE} = 3 \text{ V}; T_h = 25 ^{\circ}\text{C};$ see <u>Figure 12</u>	25	42	50	



2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	В	base		
2	С	collector	mb	C I
3	Е	emitter		В
mb	n.c.	isolated		E sym123
			SOT186A (TO-220F))

3. Ordering information

Table 3. Ordering information

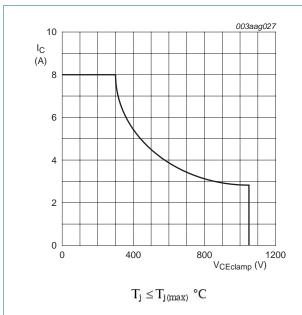
Type number	Package		
	Name	Description	Version
BUJ302AX	TO-220F	plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 3-lead TO-220 "full pack"	SOT186A

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CESM}	collector-emitter peak voltage	$V_{BE} = 0 V$	-	1050	V
V_{CEO}	collector-emitter voltage	$I_B = 0 A$	-	400	V
I _C	collector current	see Figure 1; see Figure 2; see Figure 4	-	4	Α
I _{CM}	peak collector current		-	8	Α
I _B	base current	DC	-	2	Α
I _{BM}	peak base current		-	4	Α
P _{tot}	total power dissipation	T _h ≤ 25 °C; see <u>Figure 3</u>	-	26	W
T _{stg}	storage temperature		-65	150	°C
T _j	junction temperature		-	150	°C
V_{EBO}	emitter-base voltage	$I_C = 0 \text{ A}; I_E = 2 \text{ A}; t_p < 10 \text{ ms}$	-	24	V



$$\begin{split} V_{\mathit{CL(CE)}} &\leq 1000 \; V; V_{\mathit{CC}} = 150 \; V; V_{\mathit{BB}} = \, -5 \; V; \\ L_{\mathit{B}} &= 1 \, \mu H; L_{\mathit{C}} = 200 \; \mu H \end{split} \label{eq:clce}$$

Fig 1. Reverse bias safe operating area

Fig 2. Test circuit for reverse bias safe operating area

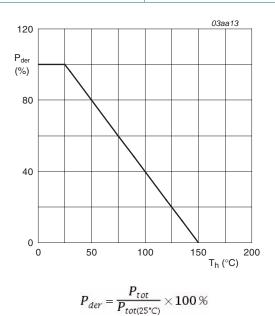
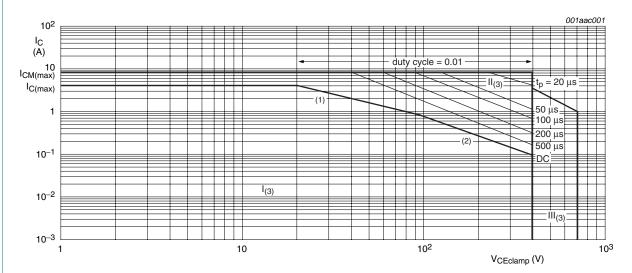


Fig 3. Normalized total power dissipation as a function of heatsink temperature



- 1)Ptot maximum and Ptot peak maximum lines
- 2)Second breakdown limits
- 3) I = Region of permissable DC operation
 - II = Extension for repetitive pulse operation
- III = Extension during turn-on in single transistor converters provided that RBE $\leq 100~\Omega$ and tp $\leq 0.6~\mu s$

Fig 4. Forward bias safe operating area for Tmb ≤ 25 °C

5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-h)}$	thermal resistance from junction to heatsink	with heatsink compound; see Figure 5	-	-	4.8	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	-	55	-	K/W

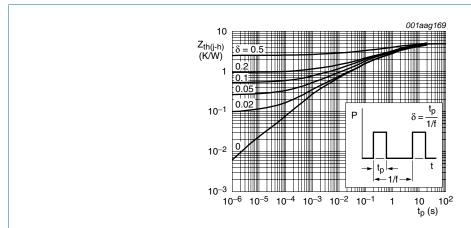


Fig 5. Transient thermal impedance from junction to heatsink as a function of pulse duration

6. Isolation characteristics

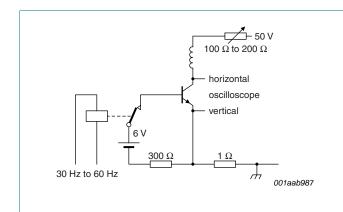
Table 6. Isolation characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{\text{isol}(\text{RMS})}$	RMS isolation voltage	50 Hz \leq f \leq 60 Hz; RH \leq 65 %; T _h = 25 °C; from all terminals to external heatsink; clean and dust free	-	-	2500	V
C _{isol}	isolation capacitance	from collector to external heatsink ; f = 1 MHz; $T_h = 25 ^{\circ}\text{C}$	-	10	-	pF

7. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
I _{CES}	collector-emitter cut-off current	$V_{BE} = 0 \text{ V}; V_{CE} = 1050 \text{ V}; T_j = 25 \text{ °C}$	-	0.2	10	μΑ
I _{CEO}	collector-emitter cut-off current	$V_{CE} = 400 \text{ V}; I_{B} = 0 \text{ A}; T_{h} = 25 \text{ °C}$	-	10	250	μΑ
$V_{(BR)EBO}$	open-collector emitter-base breakdown voltage	e $I_B = 1 \text{ mA}; I_C = 0 \text{ A}; T_h = 25 \text{ °C}$ 15 19		19	-	V
V_{CEOsus}	collector-emitter sustaining voltage	$I_B = 0 \text{ A}; I_C = 10 \text{ mA}; L_C = 25 \text{ mH};$ 400 $T_h = 25 \text{ °C}; \text{ see } \underline{\text{Figure 6}}; \text{ see } \underline{\text{Figure 7}}$		470	-	V
- OLSai	collector-emitter saturation voltage	$I_C = 1 \text{ A}$; $I_B = 0.2 \text{ A}$; $T_h = 25 \text{ °C}$; see Figure 8; see Figure 9	-	0.15	0.5	V
		$I_C = 3.5 \text{ A}$; $I_B = 1 \text{ A}$; $T_h = 25 ^{\circ}\text{C}$; see Figure 8; see Figure 9	-	0.6	1.5	V
V_{BEsat}	base-emitter saturation voltage	$I_C = 3.5 \text{ A}; I_B = 1 \text{ A}; T_h = 25 ^{\circ}\text{C};$ - 1.1 see Figure 10		1.1	1.5	V
h _{FE}	DC current gain	$I_C = 0.1 \text{ A}$; $V_{CE} = 5 \text{ V}$; $T_h = 25 ^{\circ}\text{C}$; see Figure 11	48	66	100	
		$I_C = 0.8 \text{ A}; V_{CE} = 3 \text{ V}; T_h = 25 ^{\circ}\text{C};$ see Figure 12	25	42	50	
Dynamic ch	naracteristics					
t _s	storage time	$I_C = 2.5 \text{ A}$; $I_{Bon} = 0.5 \text{ A}$; $I_{Boff} = -0.5 \text{ A}$;	-	-	3.5	μs
t _f	fall time	R_L = 60 Ω; V_{BB} = -5 V; T_h = 25 °C; resistive load; t_p = 300 μs; see Figure 13; see Figure 14	-	-	500	ns





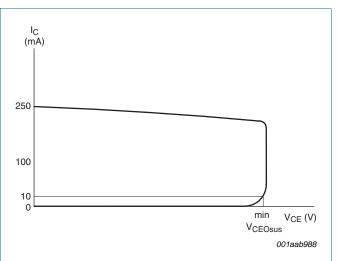


Fig 7. Oscilloscope display for collector-emitter sustaining voltage test waveform

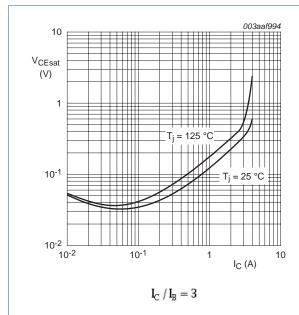


Fig 8. Collector-emitter saturation voltage as a function of collector current; typical values

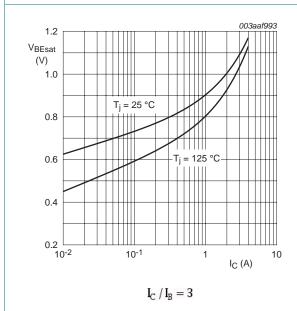


Fig 10. Base-emitter saturation voltage as a function of collector current; typical values

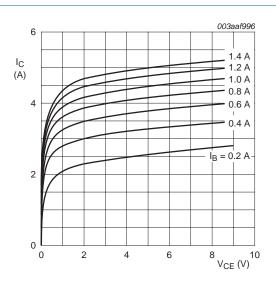


Fig 9. Collector current as a function of collector-emitter voltage; typical values

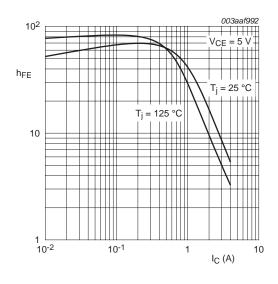


Fig 11. DC current gain as a function of collector current; typical values

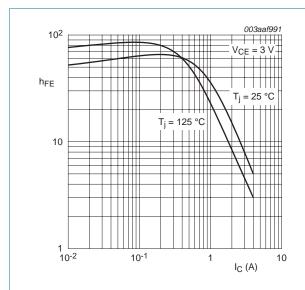
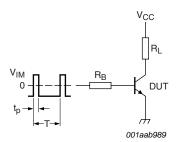


Fig 12. DC current gain as a function of collector current; typical values



 $V_{IM} = -6$ to +8 V; $V_{CC} = 250$ V; $t_p = 20$ μs ; $\delta = \frac{t_p}{T} = 0.01$ R_B and R_L calculated from I_{Con} and I_{Bon} requirements.

Fig 13. Test circuit for resistive load switching

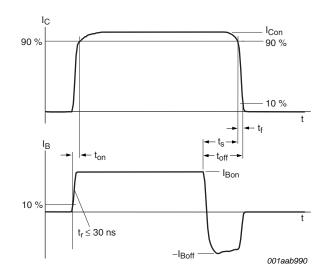
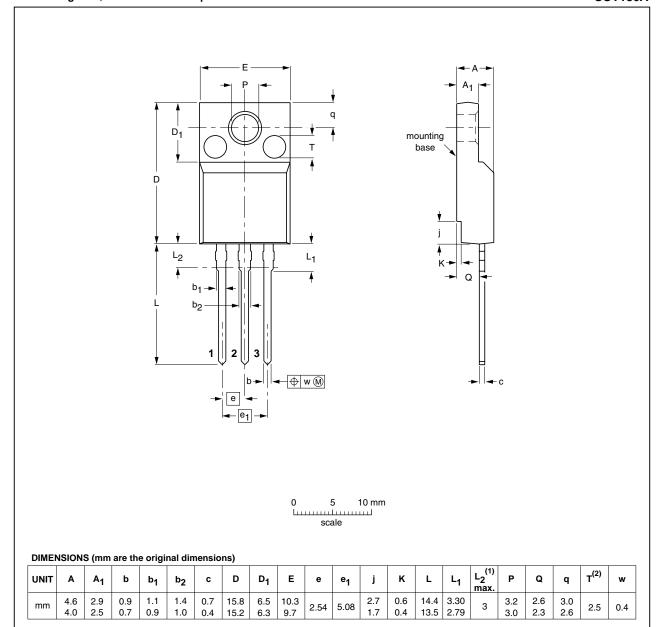


Fig 14. Switching times waveforms for resistive load

8. Package outline

Plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 3-lead TO-220 'full pack'

SOT186A



Notes

- 1. Terminal dimensions within this zone are uncontrolled.
- 2. Both recesses are \varnothing 2.5 \times 0.8 max. depth

OUTLINE		REFER	ENCES	EUROPEAN ISSUE DA	
VERSION	IEC	JEDEC	JEITA	PROJECTION	ISSUE DATE
SOT186A		3-lead TO-220F			-02-04-09 06-02-14
·					

Fig 15. Package outline SOT186A (TO-220F)

BUJ302AX

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9. Revision history

Table 8. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes	
BUJ302AX v.2	20110328	Product data sheet	-	BUJ302AX v.1	
Modifications:	 The format of this data sheet has been redesigned to comply with the new identity guidelines of NXP Semiconductors. 				
	 Legal texts have 	ve been adapted to the new	company name where	appropriate.	
BUJ302AX v.1	19980801	Objective specification	n -	-	

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10.1 Data sheet status

Document status [1] [2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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